**Product data sheet** 

## 1. Product profile

## 1.1 General description

The BGU8052 is a low noise high linearity amplifier for wireless infrastructure applications, equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 1.5 GHz and 2.5 GHz. It is housed in a 2 mm  $\times$  2 mm  $\times$  0.75 mm 8-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

## 1.2 Features and benefits

- Low noise performance: NF = 0.50 dB
- High linearity performance: IP3<sub>O</sub> = 36 dBm
- High input return loss > 15 dB
- High output return loss > 20 dB
- Unconditionally stable up to 20 GHz
- Programmable bias current (via resistor)
- Small 8-terminal leadless package 2 mm × 2 mm × 0.75 mm
- ESD protection on all terminals
- Moisture sensitivity level 1
- Fast shutdown to support TDD systems
- +5 V single supply

## 1.3 Applications

- Wireless infrastructure
- Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- General purpose wireless applications
- TDD or FDD systems
- Suitable for small cells



## Low noise high linearity amplifier

## 1.4 Quick reference data

Table 1. Quick reference data

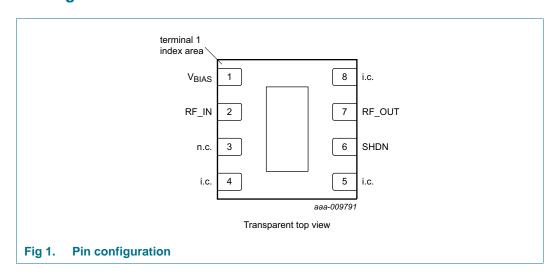
f = 1900 MHz;  $V_{CC} = 5$  V;  $T_{amb} = 25$  °C; input and output 50  $\Omega$ ; Rbias = 5.1 k $\Omega$ ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 15 with components listed in Table 9 optimized for f = 1900 MHz.

	• •	<u> </u>				
Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
$I_{CC}$	supply current	on state	36	48	60	mA
		off state	-	2.8	-	mA
G <sub>ass</sub>	associated gain	on state	17	18.5	20	dB
		off state	-	-23	-	dB
NF	noise figure		<u>[1]</u> _	0.50	0.70	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	18	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	2-tone; tone spacing = 1 M $P_i = -15$ dBm per tone	Hz; 32	36	-	dBm

<sup>[1]</sup> Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

# 2. Pinning information

## 2.1 Pinning



## 2.2 Pin description

Table 2. Pin description

Pin	Description
1	bias voltage
2	RF input
3	not connected
4, 5, 8	internally connected. Can be grounded or left open in the application.
6	shutdown
7	RF output
exposed die pad	ground
	1 2 3 4, 5, 8 6 7

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## Low noise high linearity amplifier

# 3. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
BGU8052	HWSON8	plastic thermal enhanced very very thin small outline package; no leads; 8 terminals; body $2 \times 2 \times 0.75$ mm	SOT1327-1					

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CC}$	supply voltage			-	6	V
V <sub>ctrl(sd)</sub>	shutdown control voltage			-	3	V
I <sub>CC</sub>	supply current			-	85	mΑ
$P_{i(RF)CW}$	continuous waveform RF input power			-	20	dBm
T <sub>stg</sub>	storage temperature			-40	+150	°C
T <sub>j</sub>	junction temperature			-	150	°C
Р	power dissipation	T <sub>case</sub> ≤ 125 °C	[1]	-	510	mW
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001-2010		-	0.9	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B		-	2	kV

<sup>[1]</sup> Case is ground solder pad.

# 5. Recommended operating conditions

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		4.75	5	5.25	V
$Z_0$	characteristic impedance		-	50	-	Ω
T <sub>case</sub>	case temperature		-40	-	+85	°C

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case		[1][2] 50	K/W

<sup>[1]</sup> Case is ground solder pad.

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<sup>[2]</sup> Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

## Low noise high linearity amplifier

## 7. Characteristics

#### Table 7. Characteristics

f = 1900 MHz;  $V_{CC} = 5$  V;  $T_{amb} = 25$  °C; input and output 50  $\Omega$ ; Rbias = 5.1 k $\Omega$ ; unless otherwise specified. All RF parameters are measured in an application board as shown in Figure 15 with components listed in Table 9 optimized for f = 1900 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CC</sub>	supply current	on state		36	48	60	mA
		off state		-	2.8	-	mΑ
G <sub>ass</sub>	associated gain	on state		17	18.5	20	dB
		off state		-	-23	-	dB
NF	noise figure		[1]	-	0.50	0.70	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression			-	18	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	2-tone; tone spacing = 1 MHz; $P_i = -15$ dBm per tone		32	36	-	dBm
		2-tone; tone spacing = 1 MHz; $P_i = -15$ dBm per tone	[2]	30	34	-	dBm
RLin	input return loss	on state		-	14.5	-	dB
		off state		-	8.4	-	dB
RL <sub>out</sub>	output return loss			-	23	-	dB
ISL	isolation			-	23	-	dB
t <sub>s(pon)</sub>	power-on settling time	$P_i$ = -20 dBm; SHDN (pin 6) from HIGH to LOW	[2]	-	1.4	-	μS
t <sub>s(poff)</sub>	power-off settling time	$P_i$ = -20 dBm; SHDN (pin 6) from LOW to HIGH	[2]	-	0.4	-	μS
K	Rollett stability factor	both on state and off state up to f = 20 GHz		1	-	-	
R <sub>pd(SHDN)</sub>	pull-down resistance on pin SHDN			-	20	-	kΩ

<sup>[1]</sup> Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

Table 8. Shutdown control

 $V_{CC} = 5 \ V; \ T_{amb} = 25 \ ^{\circ}C.$ 

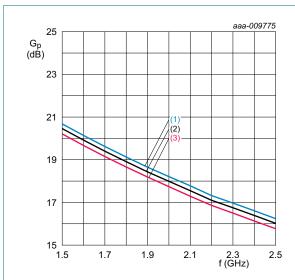
State	V <sub>ctrl(sd)</sub> [1]
	(V)
on state	≤ 0.6
off state	≥ 1.2

<sup>[1]</sup> Voltage on pin 6 (SHDN).

<sup>[2]</sup> For TDD systems where fast switching is required, it is recommended to change C1 and C2 to 100 pF.

## Low noise high linearity amplifier

## 7.1 Graphs



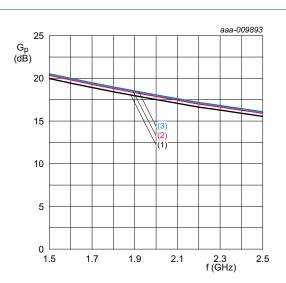
 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = +25 \, ^{\circ}C$$

(3)  $T_{amb} = +85 \, ^{\circ}C$ 

Fig 2. Power gain as a function of frequency; typical values



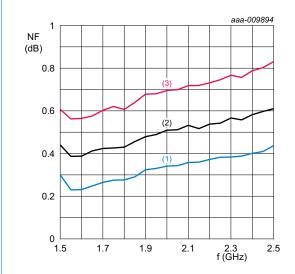
 $V_{CC}$  = 5 V;  $T_{amb}$  = 25 °C.

(1) 
$$I_{CC} = 30 \text{ mA}$$

(2) 
$$I_{CC} = 45 \text{ mA}$$

(3)  $I_{CC} = 60 \text{ mA}$ 

Fig 3. Power gain as a function of frequency; typical values



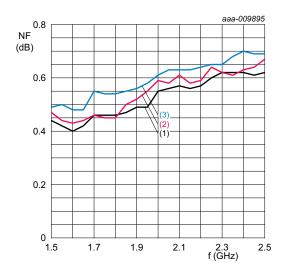
 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$ 

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = +25 \, ^{\circ}C$$

(3)  $T_{amb} = +85 \, ^{\circ}C$ 

Fig 4. Noise figure as a function of frequency; typical values



 $V_{CC} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}.$ 

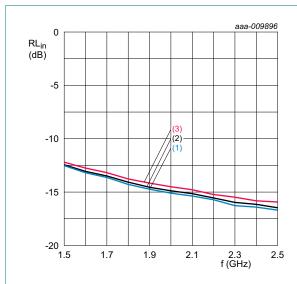
(1) 
$$I_{CC} = 30 \text{ mA}$$

(2)  $I_{CC} = 45 \text{ mA}$ 

(3)  $I_{CC} = 60 \text{ mA}$ 

Fig 5. Noise figure as a function of frequency; typical values

## Low noise high linearity amplifier



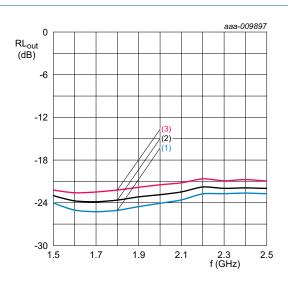
$$V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = +25 \, ^{\circ}C$$

(3) 
$$T_{amb} = +85 \, ^{\circ}C$$

Fig 6. Input return loss as a function of frequency; typical values



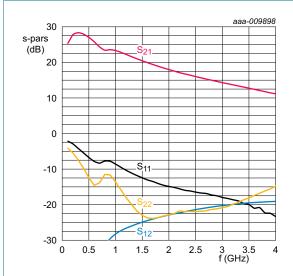
$$V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = +25 \, ^{\circ}C$$

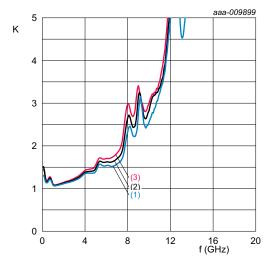
(3) 
$$T_{amb} = +85 \, ^{\circ}C$$

Fig 7. Output return loss as a function of frequency; typical values



 $V_{CC} = 5 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}; I_{CC} = 48 \text{ mA}.$ 

Fig 8. Wideband S-parameters as function of frequency; typical values



$$V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$$

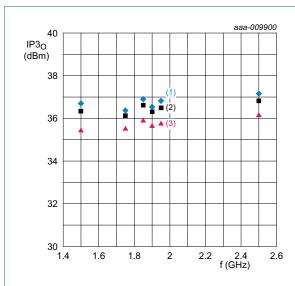
(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = +25 \, ^{\circ}C$$

(3) 
$$T_{amb} = +85 \, ^{\circ}C$$

Fig 9. Rollet stability factor as a function of frequency; typical values

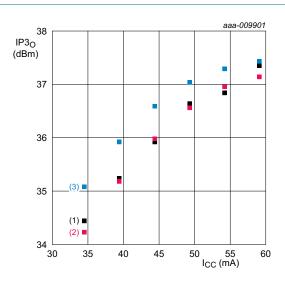
### Low noise high linearity amplifier



 $V_{CC} = 5 \text{ V}$ ;  $P_i = -15 \text{ dBm per tone}$ ;  $I_{CC} = 48 \text{ mA}$ .

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = +25 \, ^{\circ}C$
- (3)  $T_{amb} = +85 \, ^{\circ}C$

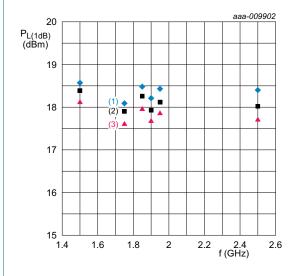
Fig 10. Output third-order intercept point as a function of frequency; typical values



 $V_{CC} = 5 \text{ V}$ ;  $P_i = -15 \text{ dBm per tone}$ ;  $T_{amb} = 25 \,^{\circ}\text{C}$ .

- (1) f = 1500 MHz
- (2) f = 1900 MHz
- (3) f = 2500 MHz

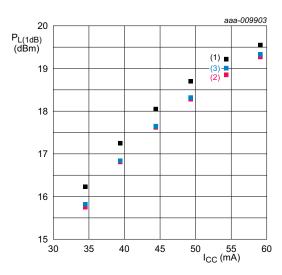
Fig 11. Output third-order intercept point as a function of supply current; typical values



 $V_{CC} = 5 \text{ V}; I_{CC} = 48 \text{ mA}.$ 

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = +25 \, ^{\circ}C$
- (3)  $T_{amb} = +85 \, ^{\circ}C$

Fig 12. Output power at 1 dB gain compression as a function of frequency; typical values

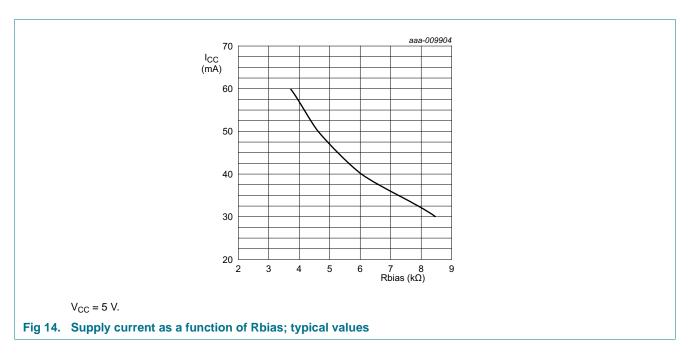


 $V_{CC} = 5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}.$ 

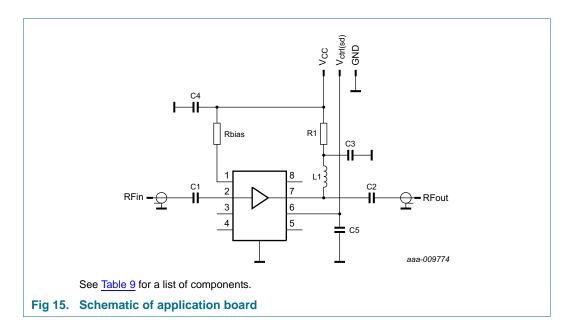
- (1) f = 1500 MHz
- (2) f = 1900 MHz
- (3) f = 2500 MHz

Fig 13. Output power at 1 dB gain compression as a function of supply current; typical values

## Low noise high linearity amplifier



# 8. Application information



**Table 9.** List of components See <u>Figure 15</u> for schematics.

Component	Description	Value	Remarks
C1, C2	capacitor	100 nF	
		100 pF	recommended for TDD systems
C3	capacitor	10 pF	
C4	capacitor	5.6 nF	
C5	capacitor	10 pF	

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## Low noise high linearity amplifier

**Table 9.** List of components ...continued See Figure 15 for schematics.

Component	Description	Value	Remarks	
L1	inductor	15 nH		
R1	resistor	10 Ω		
Rbias	resistor	5.1 kΩ		

### Table 10. Typical performance BGU8052 application board

All RF parameters are measured at the application board as shown in <u>Figure 15</u> with the components as listed in <u>Table 9</u> while optimized for: f = 1900 MHz;  $V_{CC} = 5 \text{ V}$ ;  $I_{CC} = 48 \text{ mA}$  and  $T_{amb} = 25 \text{ }^{\circ}\text{C}$ .

Symbol	Parameter		f (MHz)							
			1500	1750	1850	1900	1950	2100	2300	2500
G <sub>ass</sub>	associated gain		20.5	19.2	18.7	18.4	18.2	17.6	16.8	16.0
$RL_{in}$	input return loss		12.4	27.6	14.3	14.6	14.7	15.2	16.0	16.5
RL <sub>out</sub>	output return loss		23.0	47.5	23.4	23.2	23.0	22.5	22.0	22.0
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		18.4	17.9	18.3	17.9	18.1	18.7	18.2	18.0
IP3 <sub>O</sub>	output third-order	<u>[1]</u>	36.3	36.1	36.6	36.3	36.5	36.5	35.2	36.8
	intercept point	[1][2]	36.9	36.0	37.3	38.1	34.9	34.5	34.0	33.0
NF	noise figure	[3]	0.44	0.43	0.46	0.48	0.49	0.53	0.57	0.61

<sup>[1] 2-</sup>Tone; tone spacing = 1 MHz;  $P_i = -15$  dBm per tone.

<sup>[2]</sup> For applications where fast switching is required, it is recommended to change C1 and C2 to 100 pF.

<sup>[3]</sup> Connector and board losses not de-embedded.

## Low noise high linearity amplifier

# 9. Package outline

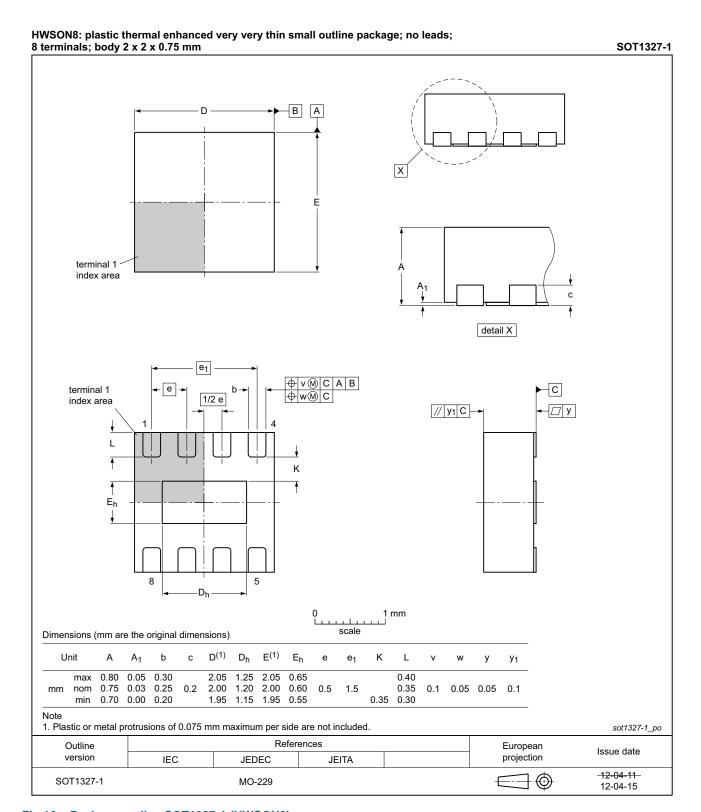


Fig 16. Package outline SOT1327-1 (HWSON8)

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## Low noise high linearity amplifier

# 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile Communication
LNA	Low Noise Amplifier
LTE	Long Term Evolution
RF	Radio Frequency
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

# 11. Revision history

## Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGU8052 v.2	20131230	Product data sheet	-	BGU8052 v.1	
Modifications:	<ul> <li><u>Table 4 on page 3</u>: The maximum value for V<sub>ctrl(sd)</sub> has been corrected to 3 V.</li> <li><u>Table 10 on page 9</u>: A correction has been made for the value of G<sub>ass</sub> at f = 1750 MHz.</li> </ul>				
BGU8052 v.1	20131127	Product data sheet	-	-	

#### Low noise high linearity amplifier

## 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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## Low noise high linearity amplifier

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## Low noise high linearity amplifier

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Skype ameyasales1 ameyasales2

## Customer Service :

Email service@ameya360.com

# Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com